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Kind regards,

Team Nexperia



150 V, 1 A NPN high-voltage low VCEsat BISS transistor 10 January 2017

Product data sheet

1. General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9115TLH

2. Features and benefits

- High voltage •
- Low collector-emitter saturation voltage V_{CEsat} •
- High collector current capability I_C and I_{CM}
- Small SMD plastic package
- AEC-Q101 qualified •

3. Applications

- Power management •
- LCD backlighting
- LED driver for LED chain module •
- Switch Mode Power Supply (SMPS) •

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	150	V
I _C	collector current			-	-	1	А
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-	2	А
h _{FE}	DC current gain	V_{CE} = 10 V; I _C = 50 mA; T _{amb} = 25 °C		70	-	300	



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5. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	В	base	3	С			
2	E	emitter		в			
3	С	collector	1 2 TO-236AB (SOT23)	E sym123			

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBHV8115TLH	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
PBHV8115TLH	FB%

[1] % = placeholder for manufacturing site code

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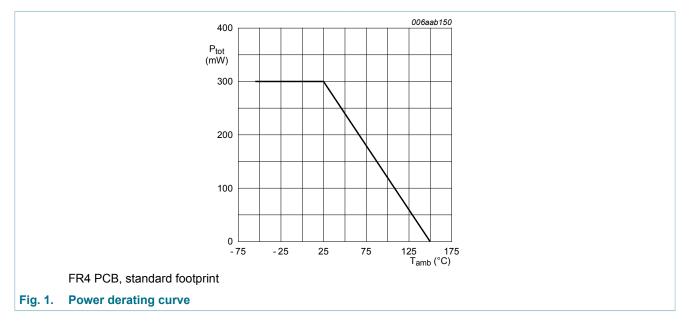
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	400	V
V _{CEO}	collector-emitter voltage	open base		-	150	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	200	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	А
I _{BM}	peak base current			-	400	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

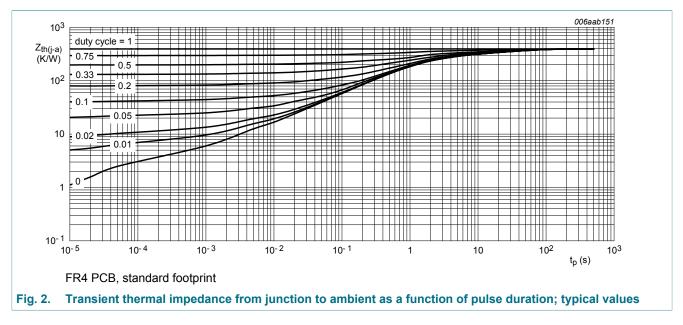


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9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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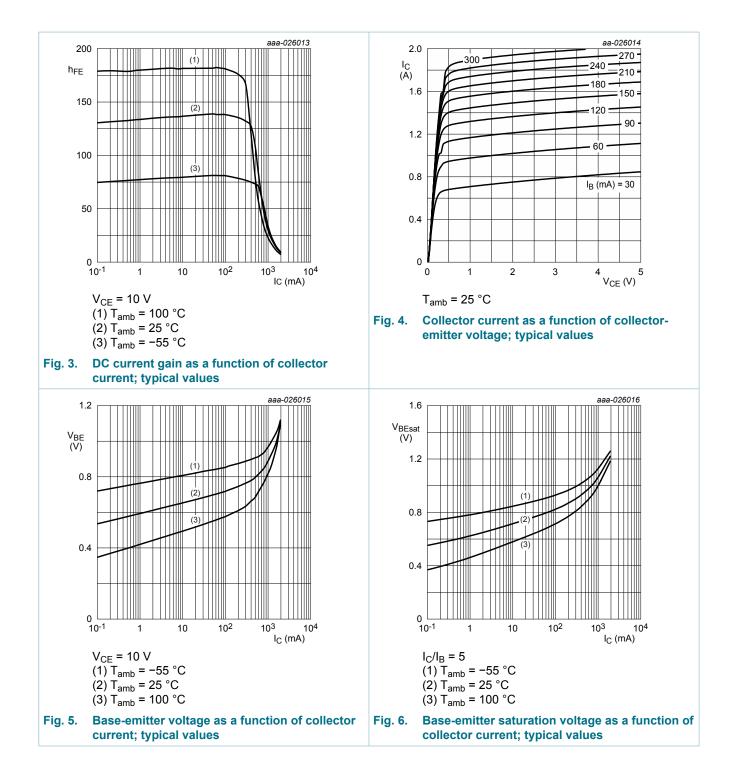
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 120 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
current	current	V _{CB} = 120 V; I _E = 0 A; T _j = 150 °C	-	-	10	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 120 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 50 mA; T _{amb} = 25 °C	70	-	300	
		V _{CE} = 10 V; I _C = 100 mA; T _{amb} = 25 °C	60	-	300	
		V_{CE} = 10 V; I _C = 500 mA; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	50	-	300	
		V_{CE} = 10 V; I _C = 1 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	10	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 100 mA; I_{B} = 10 mA; T_{amb} = 25 °C	-	-	60	mV
		I_{C} = 100 mA; I_{B} = 20 mA; T_{amb} = 25 °C	-	-	50	mV
		I_C = 1 A; I_B = 200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	350	mV
V _{BEsat}	base-emitter saturation voltage		-	-	1.2	V
t _d	delay time	V _{CC} = 6 V; I _C = 0.5 A; I _{Bon} = 0.1 mA;	-	10	-	ns
t _r	rise time	I _{Boff} = -0.1 mA; T _{amb} = 25 °C	-	565	-	ns
t _{on}	turn-on time	V _{CC} = 6 V; I _C = 0.5 A; I _{Bon} = 0.1 A;	-	575	-	ns
t _s	storage time	I _{Boff} = -0.1 A; T _{amb} = 25 °C	-	1530	-	ns
t _f	fall time		-	700	-	ns
t _{off}	turn-off time		-	2230	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 10 mA; f = 100 MHz; T _{amb} = 25 °C	-	30	-	MHz
C _c	collector capacitance	V_{CB} = 20 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	6	-	pF
C _e	emitter capacitance	V _{EB} = 0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	150	-	pF

PBHV8115TLH

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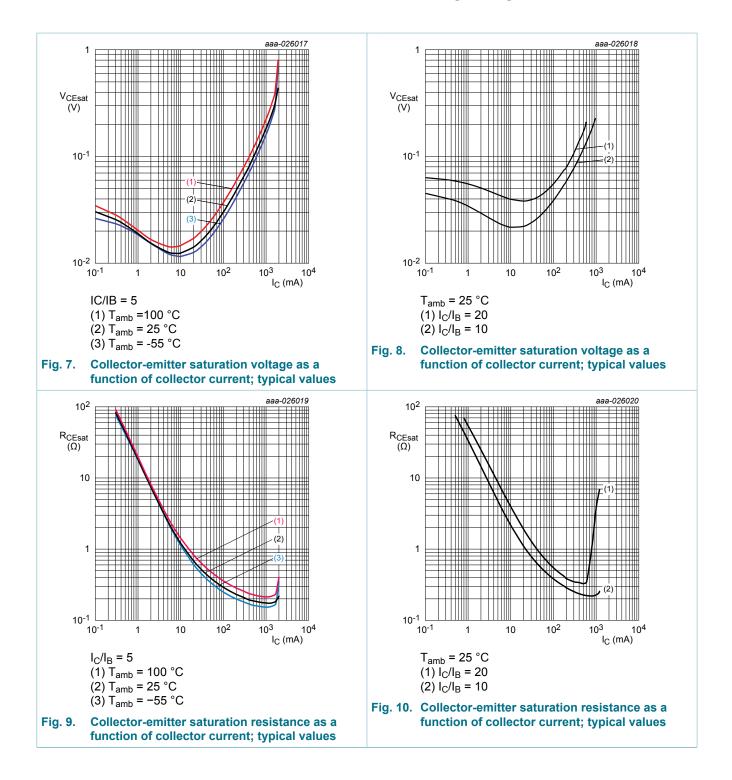
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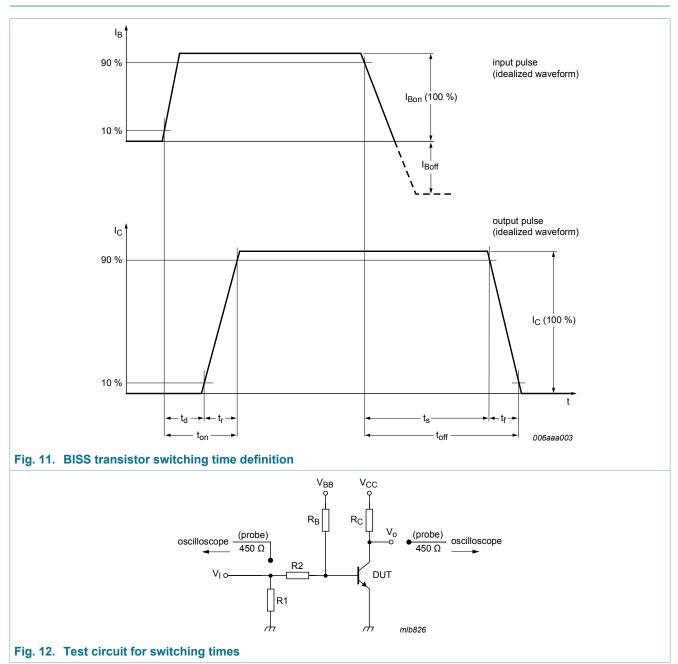
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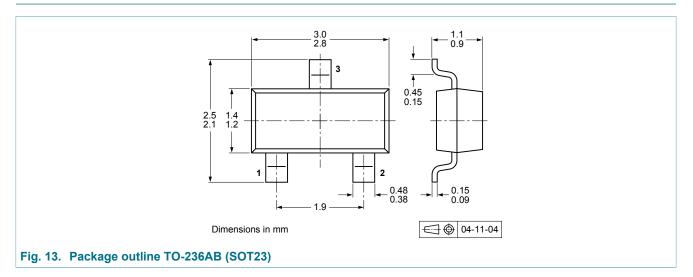
11. Test information

Quality information

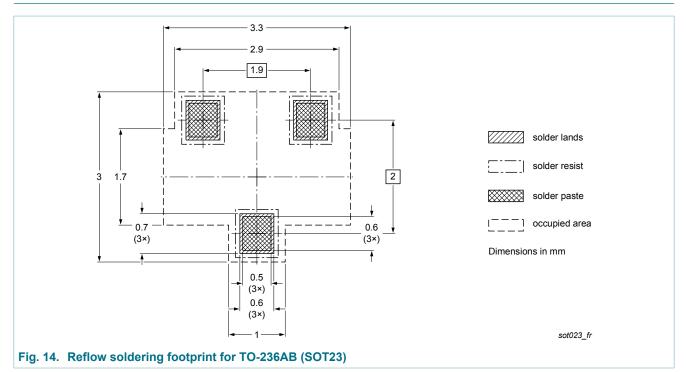
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

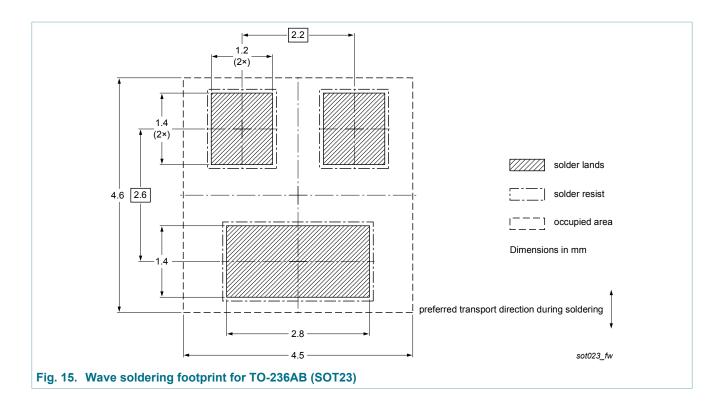


13. Soldering



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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBHV8115TLH v.1	2017010	Product data sheet	-	-			

150 V, 1 A NPN high-voltage low VCEsat BISS transistor

15. Legal information

Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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PBHV8115TLH

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